



제25회 한국반도체학술대회

The 25th Korean Conference on Semiconductors

2018년 2월 5일(월)-7일(수), 강원도 하이원리조트 컨벤션 호텔

2018년 2월 6일(화), 09:00-10:45

Room I (청옥II+III, 6층)

K. Memory (Design & Process Technology) 분과 [TI1-K] ReRAM I - Preparing for Mass Production

<p>TI1-K-1 09:00-09:30</p>	<p>[초청] Highly Reliable Multi-Bit Operation in HfO₂ Based Resistive Switching Device Gun Hwan Kim, Ji Woon Choi, Bo Keun Park, Taek-Mo Cheong, and Young Kuk Lee <i>Center for Thin-Film Materials, KRICT</i></p>
<p>TI1-K-2 09:30-09:45</p>	<p>Roles of Conducting Filament and Non-Filament Regions in the Ta₂O₅ and HfO₂ Resistive-Switching Memory for Switching Reliability Tae Hyung Park¹, Hae Jin Kim¹, Soo Gil Kim², Byung Joon Choi³, and Cheol Seong Hwang¹ <i>¹Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, Seoul National University, ²SK Hynix Inc., ³Department of Materials Science and Engineering, Seoul National University of Science and Technology</i></p>
<p>TI1-K-3 09:45-10:00</p>	<p>Controlling Filament Forming Direction of Restive Switching Memory Device via Nanomesh Patterning Tae Jin Kim , Byoung Kuk You, Jong Min Kim, Daniel J. Joe, and Keon Jae Lee <i>Department of Material Science and Engineering, KAISE</i></p>
<p>TI1-K-4 10:00-10:15</p>	<p>Selector for Bipolar Resistive Switching Material Having Current Saturation Functionality with Pt/Ti/TiO₂/HfO₂/TiN Device Daeun Kwon, Jung Ho Yoon, Tae Hyung Park, Yumin Kim, Young Jae Kwon, Hae Jin Kim, and Cheol Seong Hwang <i>Department of Materials Science and Engineering and Inter-university Semiconductor Research Center, Seoul National University</i></p>
<p>TI1-K-5 10:15-10:30</p>	<p>저항 변화층의 Initial Current Level과 저항 변화 특성 김명주, 한언빈, 김태우, 이한춘, 이상기, 이윤종 <i>DB Hitek, 특화공정개발파트</i></p>